650V N-channel Super Junction MOSFET

MAIN CHARACTERISTICS

I_D	11A
V_{DS}	650V
R_{DSON}-typ(@V_{GS}=10V)	390mΩ(Typ:340mΩ)

FEATURES

- Ultra low RDS(on)
- Ultra low gate charge
- 100% UIS tested

APPLICATION

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply(UPS
- Power Factor Correction(PFC)

MECHANICAL DATA

- Case: TO-252/AD
- Mounting Position: Any
- Molded Plastic: UL Flammability Classification Rating 94V-0
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Solder bath temperature 275 maximum,10s per JESD 22-B106

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbol	Value	Unit

Ratin

Ratings and Characteristic Curves

Fig 7: Body Diode Characteristics

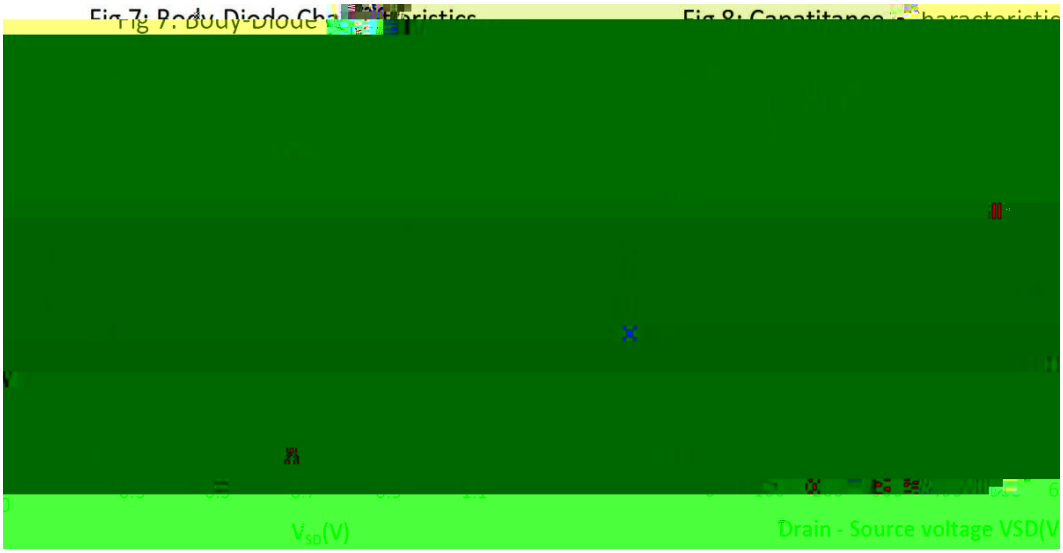


Fig 8: Capatitance Characteristic

Fig 9: Gate Quantity of electric charger vs. Gate Voltage

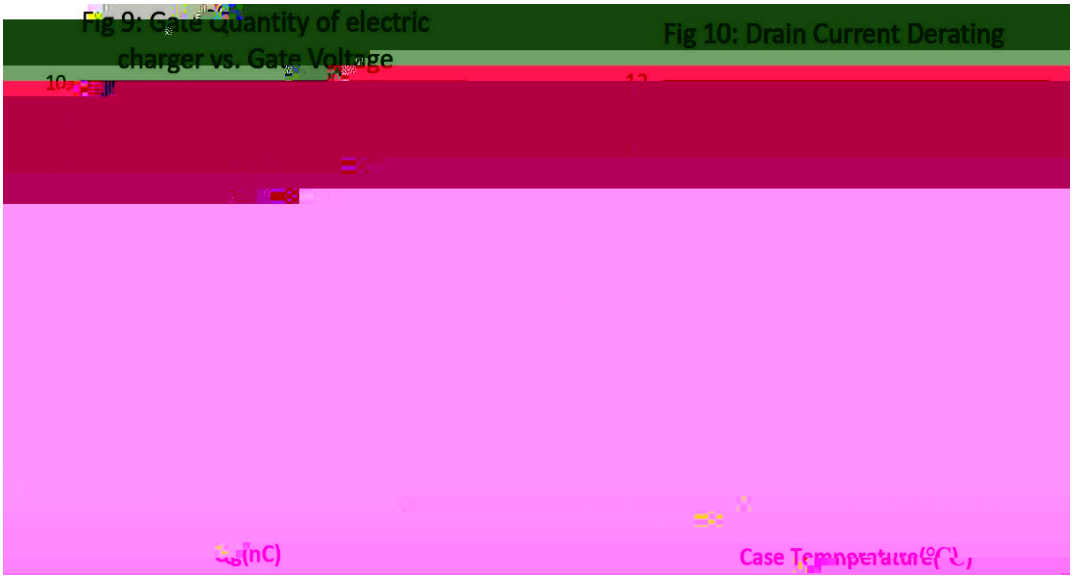


Fig 10: Drain Current Derating

Fig 11: Power Dissipation

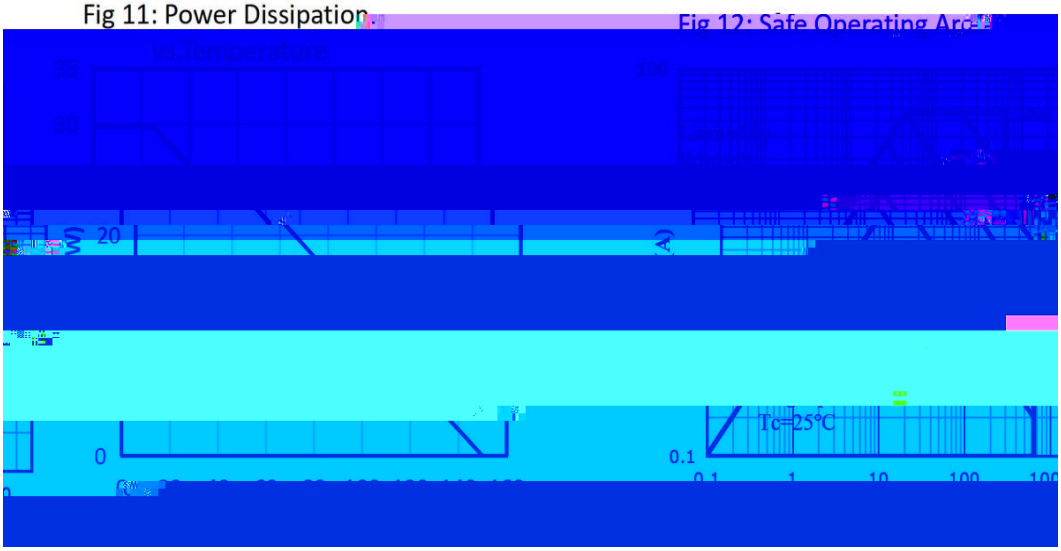


Fig 12: Safe Operating Area

YFW65R380AD

E

The information presented in this document is for reference only. GuangDong Youfeng Microelectronics Co.,Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise. The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices),YFW or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale. This publication supersedes & replaces all information previously supplied. For additional information, please visit our website https://www.yfwdiode.com, or consult YFW sales office for further assistance.